

INFORMATION DISCLOSURE CITATION FORM FOR PATENT APPLICATION (FORM PTO-1449) (Substitute)		Docket No.: YOR920030208US1	Serial No.:			
		Applicant(s): Hyungjun KIM et al.				
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U.S. PATENTS						
Initials	Patent Number	Issue Date	Name	Class	Sub-class	Filing date
FOREIGN PATENT DOCUMENTS						
Initials	Document Number	Date	Country	Name		Translation? Yes/No/n/a
OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)						
	Kim et al., Diffusion barrier properties of transition metal thin films grown by plasma-enhanced atomic layer deposition, J. Vac. Sci. Technol. B 20(4), J/A 2002					
	Kim et al., Growth kinetics and initial stage growth during plasma-enhanced Ti atomic layer deposition, J. Vac. Sci. Technol. A 20(3), May/June 2002					
	Rossnagel et al., Plasma-enhanced atomic layer deposition of Ta and Ti for inter-connect diffusion barriers, J. Vac. Sci. Technol. B 18(4), July/Aug 2002					
Examiner's Signature:				Date Considered:		
Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).						